

50 V, 3 A PNP low VCEsat transistor

16 May 2022

Product data sheet

1. General description

PNP low V_{CEsat} transistor in a SOT89 plastic package.

NPN complement: PBSS4350X

2. Features and benefits

- SOT89 (SC-62) package
- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability: I_C and I_{CM}
- Higher efficiency leading to less heat generation
- Reduced printed-circuit board requirements
- AEC-Q101 qualified

3. Applications

- Power management
 - DC/DC converters
 - Supply line switching
 - Battery charger
 - LCD backlighting
- Peripheral drivers
 - Driver in low supply voltage applications (e.g. lamps and LEDs)
 - · Inductive load driver (e.g. relays, buzzers and motors)

4. Quick reference data

Table 1. Quick reference data							
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
V _{CEO}	collector-emitter voltage	open base		-	-	-50	V
I _C	collector current			-	-	-3	A
I _{CM}	peak collector current	limited by T _{j(max)}		-	-	-5	A
R _{CEsat}	collector-emitter saturation resistance	I_C = -2 A; I_B = -200 mA; pulsed; t_p ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C		-	90	135	mΩ

nexperia

5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E	emitter		С
2	С	collector		
3	В	base		B
			SOT89	sym132

6. Ordering information

Table 3. Ordering information							
Type number	Package	age					
	Name	Description	Version				
PBSS5350X	SOT89	plastic, surface-mounted package; 3 leads; 1.5 mm pitch; 4.5 mm x 2.5 mm x 1.5 mm body	<u>SOT89</u>				

7. Marking

Table 4. Marking codes	
Type number	Marking code
PBSS5350X	S46

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	-50	V
V _{CEO}	collector-emitter voltage	open base		-	-50	V
V _{EBO}	emitter-base voltage	open collector		-	-5	V
I _C	collector current			-	-3	А
I _{CM}	peak collector current	limited by T _{j(max)}		-	-5	А
I _B	base current			-	-0.5	А
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	550	mW
			[2]	-	1	W
			[3]	-	1.4	W
			[4]	-	1.6	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

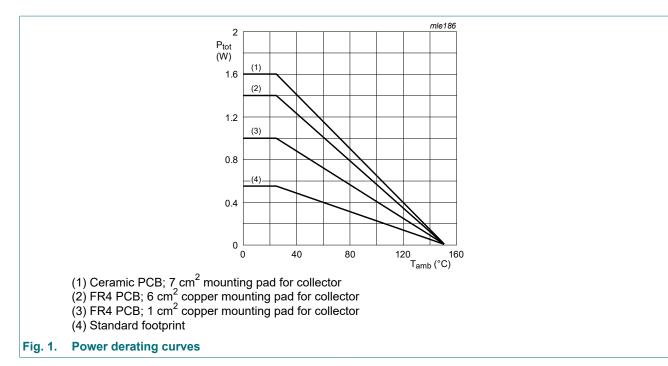
Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint. [1]

Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm² [2]

Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm². Device mounted on a ceramic printed-circuit board 7 cm², single-sided copper, tin-plated. [3]

[4]

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9. Thermal characteristics

Table 6. The	rmal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air [1] [2] [3] [4]	[1]	-	-	225	K/W
			[2]	-	-	125	K/W
			[3]	-	-	90	K/W
			[4]	-	-	80	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	16	K/W

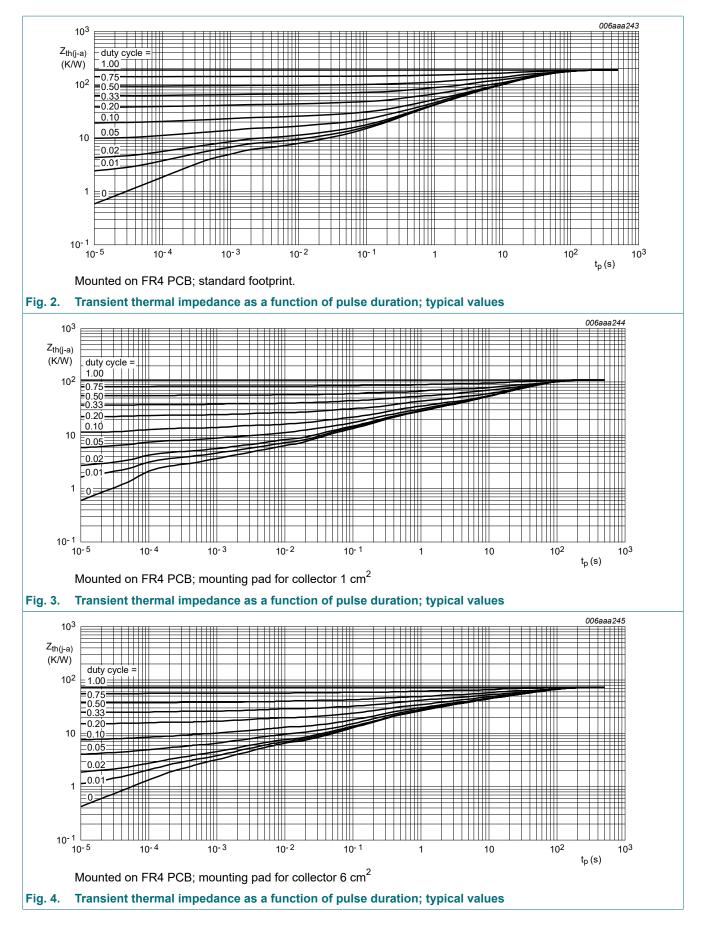
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

[4] Device mounted on a ceramic printed-circuit board 7 cm², single-sided copper, tin-plated.

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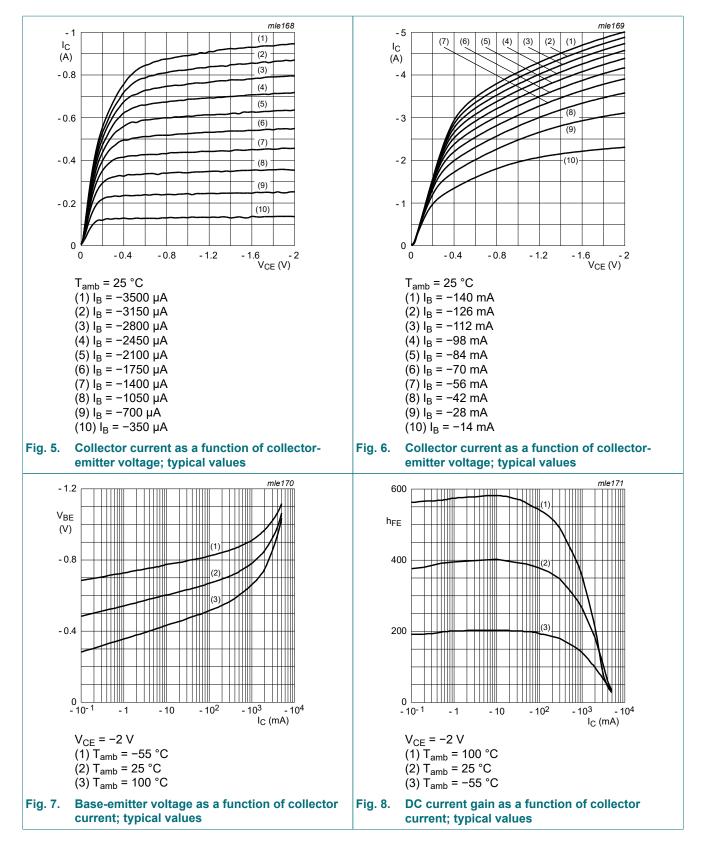


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10. Characteristics

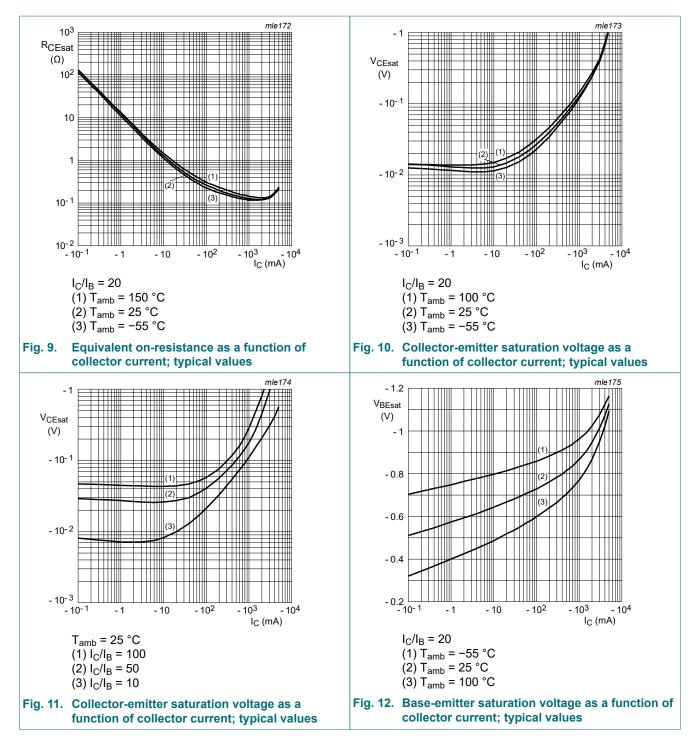
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V _{(BR)CBO}	collector-base breakdown voltage	I _C = -100 μA; I _E = 0 A; T _{amb} = 25 °C	-50	-	-	V
V _{(BR)CEO}	collector-emitter breakdown voltage	I_{C} = -10 mA; I_{B} = 0 A; T_{amb} = 25 °C	-50	-	-	V
V _{(BR)EBO}	emitter-base breakdown voltage (collector open)	I _E = -100 μA; I _C = 0 A; T _{amb} = 25 °C	-5	-	-	V
I _{CBO}	collector-base cut-off	V _{CB} = -50 V; I _E = 0 A; T _{amb} = 25 °C	-	-	-100	nA
	current	V _{CB} = -50 V; I _E = 0 A; T _i = 150 °C	-	-	-50	μA
I _{CES}	collector-emitter cut-off current	V_{CE} = -50 V; V_{BE} = 0 V; T_{amb} = 25 °C	-	-	-100	nA
I _{EBO}	emitter-base cut-off current	V_{EB} = -5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	-100	nA
h _{FE}	DC current gain	$ \begin{array}{l} V_{CE} = -2 \; V; \; I_C = 0.1 \; A; \; single \; pulse; \; t_p \leq \\ 300 \; \mu s; \; \delta \leq \; 0.02; \; T_{amb} = 25 \; ^\circ C \end{array} $	200	-	-	
		V _{CE} = -2 V; I _C = -0.5 A; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	200	-	-	
		V_{CE} = -2 V; I _C = -1 A; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	200	-	450	
		V_{CE} = -2 V; I _C = -2 A; pulsed; t _p ≤ 300 µs; δ ≤ 0.02; T _{amb} = 25 °C	130	-	-	
		V _{CE} = -2 V; I _C = -3 A; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	80	-	-	
V _{CEsat}	collector-emitter saturation voltage	I _C = -0.5 A; I _B = -50 mA; T _{amb} = 25 °C	-	-	-90	mV
		I _C = -1 A; I _B = -50 mA; T _{amb} = 25 °C	-	-	-180	mV
		I _C = -2 A; I _B = -100 mA; T _{amb} = 25 °C	-	-	-320	mV
		I _C = -2 A; I _B = -200 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	-	-270	mV
		I _C = -3 A; I _B = -300 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	-	-390	mV
R _{CEsat}	collector-emitter saturation resistance	I _C = -2 A; I _B = -200 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	90	135	mΩ
V _{BEsat}	base-emitter saturation	I _C = -2 A; I _B = -100 mA; T _{amb} = 25 °C	-	-	-1.1	V
	voltage	I _C = -3 A; I _B = -300 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	-	-1.2	V
V _{BEon}	base-emitter turn-on voltage	V_{CE} = -2 V; I _C = -1 A; T _{amb} = 25 °C	-	-	-1.1	V
fT	transition frequency	V _{CE} = -5 V; I _C = -100 mA; f = 100 MHz; T _{amb} = 25 °C	100	-	-	MHz
C _c	collector capacitance	V _{CB} = -10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	-	35	pF

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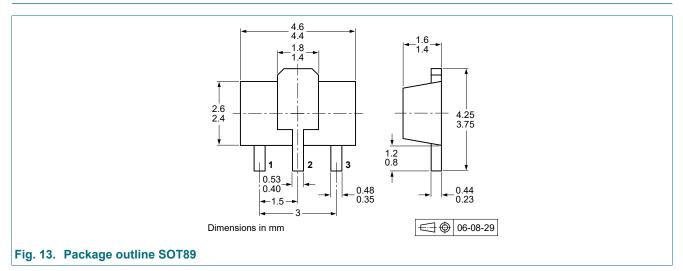
11. Test information

Quality information

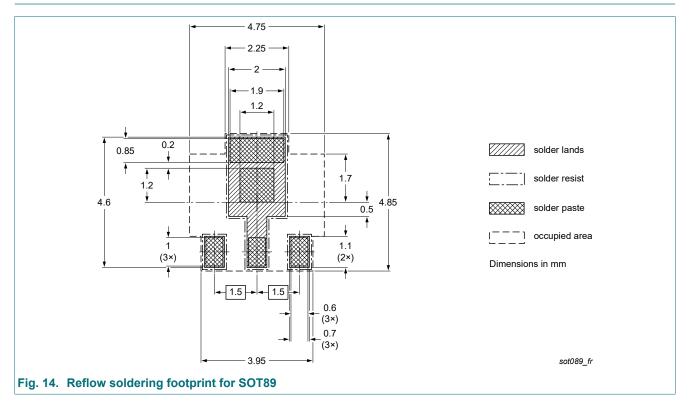
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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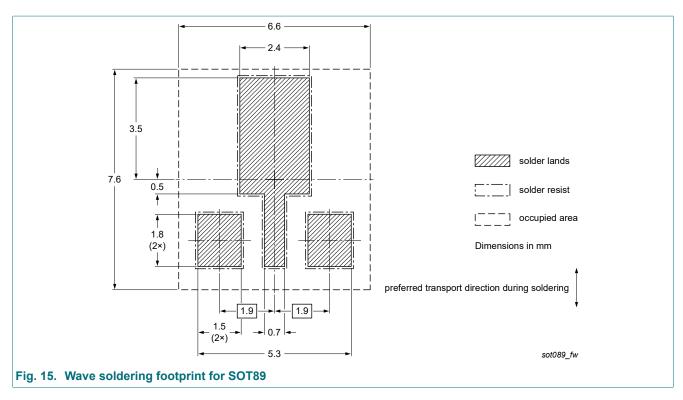
12. Package outline



13. Soldering



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14. Revision history

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Release date	Data sheet status	Change notice	Supersedes			
20220516	Product data sheet	-	PBSS5350X v.2			
 The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia. Legal texts have been adapted to the new company name where appropriate. 						
20041104	Product data sheet	-	PBSS5350X v.1			
20031121	Product data sheet	-	-			
	 Release date 20220516 The format of this da Nexperia. Legal texts have bee 20041104 	Release date Data sheet status 20220516 Product data sheet • The format of this data sheet has been redesin Nexperia. • Legal texts have been adapted to the new con 20041104	Release date Data sheet status Change notice 20220516 Product data sheet - • The format of this data sheet has been redesigned to comply with the in Nexperia. - • Legal texts have been adapted to the new company name where approxed to the			

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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